TOSHIBA CMOS Digital Integrated Circuit   Silicon Monolithic

TC74VHC245F,TC74VHC245FT,TC74VHC245FK

Octal Bus Transceiver

The TC74VHC245 is an advanced high speed CMOS OCTAL BUS TRANSCEIVER fabricated with silicon gate C^2MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

It is intended for two-way asynchronous communication between data busses. The direction of data transmission is determined by the level of the DIR input.

The enable input ($\overline{G}$) can be used to disable the device so that the busses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.

Features (Note 1) (Note 2) (Note 3)

- High speed: t_{pd} = 4.0 ns (typ.) at V_{CC} = 5 V
- Low power dissipation: I_{CC} = 4 μA (max) at Ta = 25°C
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: $V_{CC (opr)}$ = 2 V to 5.5 V
- Low noise: V_{OLP} = 1.2 V (max)
- Pin and function compatible with 74ALS245

    Note 1:   Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.

    Note 2:   All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.

    Note 3:   A parasitic diode is formed between the bus and V_{CC} terminals. Therefore bus terminal can not be used to interface 5 V to 3 V systems directly.
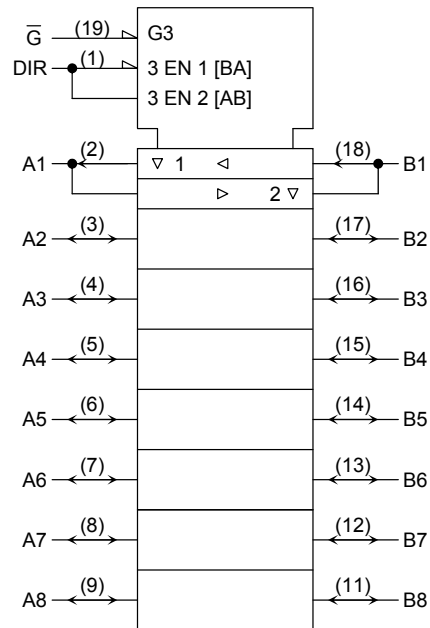
TC74VHC245F

SOP20-P-300-1.27A

TC74VHC245FT

TSSOP20-P-0044-0.65A

TC74VHC245FK
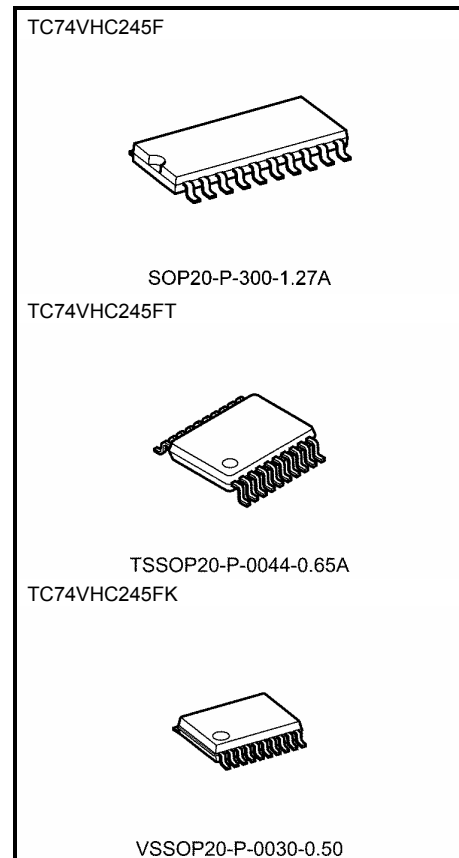
VSSOP20-P-0030-0.50

Weight
SOP20-P-300-1.27A   : 0.22 g (typ.)
TSSOP20-P-0044-0.65A   : 0.08 g (typ.)
VSSOP20-P-0030-0.50   : 0.03 g (typ.)

Pin Assignment

IEC Logic Symbol

(top view)
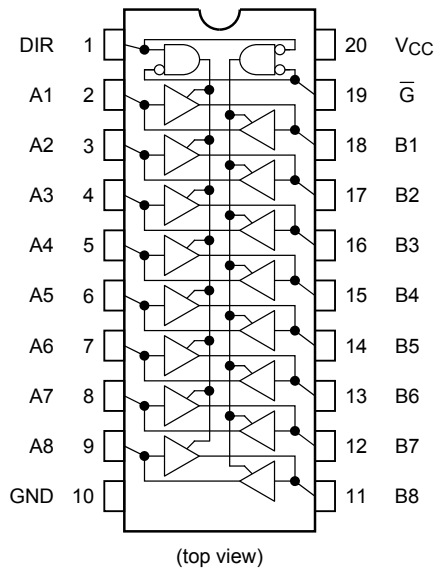
Truth Table

Inputs		Function		Output
$\overline{G}$	DIR	A Bus	B Bus	
L	L	Output	Input	A = B
L	H	Input	Output	B = A
H	X	Z		Z

X: Don't care

Z: High impedance

Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	−0.5 to 7.0	V
DC input voltage (DIR, $\overline{G}$)	V_{IN}	−0.5 to 7.0	V
DC bus I/O voltage	$V_{I/O}$	−0.5 to V_{CC} + 0.5	V
Input diode current	I_{IK}	−20	mA
Output diode current	I_{OK}	±20	mA
DC output current	I_{OUT}	±25	mA
DC V_{CC}/ground current	I_{CC}	±75	mA
Power dissipation	P_D	180	mW
Storage temperature	T_{stg}	−65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	2.0 to 5.5	V
Input voltage (DIR, $\overline{G}$)	V_{IN}	0 to 5.5	V
Bus I/O voltage	$V_{I/O}$	0 to V_{CC}	V
Operating temperature	T_{opr}	−40 to 85	°C
Input rise and fall time	dt/dv	0 to 100 (V_{CC} = 3.3 ± 0.3 V) 0 to 20 (V_{CC} = 5 ± 0.5 V)	ns/V

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs and bus inputs must be tied to either VCC or GND. Please connect both bus inputs and the bus outputs with VCC or GND when the I/O of the bus terminal changes by the function. In this case, please note that the output is not short-circuited.

Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition		V_{CC} (V)	Ta = 25°C			Ta = −40 to 85°C		Unit
					Min	Typ.	Max	Min	Max	
High-level input voltage	V_{IH}	—		2.0	1.50	—	—	1.50	—	V
				3.0 to 5.5	V_{CC} × 0.7	—	—	V_{CC} × 0.7	—	
Low-level input voltage	V_{IL}	—		2.0	—	—	0.50	—	0.50	V
				3.0 to 5.5	—	—	V_{CC} × 0.3	—	V_{CC} × 0.3	
High-level output voltage	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −50 μA	2.0	1.9	2.0	—	1.9	—	V
				3.0	2.9	3.0	—	2.9	—	
				4.5	4.4	4.5	—	4.4	—	
			I_{OH} = −4 mA	3.0	2.58	—	—	2.48	—	
			I_{OH} = −8 mA	4.5	3.94	—	—	3.80	—	
Low-level output voltage	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 50 μA	2.0	—	0.0	0.1	—	0.1	V
				3.0	—	0.0	0.1	—	0.1	
				4.5	—	0.0	0.1	—	0.1	
			I_{OL} = 4 mA	3.0	—	—	0.36	—	0.44	
			I_{OL} = 8 mA	4.5	—	—	0.36	—	0.44	
3-state output off-state current	I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = V_{CC} or GND		5.5	—	—	±0.25	—	±2.50	μA
Input leakage current	I_{IN}	V_{IN} = 5.5 V or GND		0 to 5.5	—	—	±0.1	—	±1.0	μA
Quiescent supply current	I_{CC}	V_{IN} = V_{CC} or GND		5.5	—	—	4.0	—	40.0	μA

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AC Characteristics (input: $t_r = t_f$ = 3 ns)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = −40 to 85°C		Unit
		V_{CC} (V)	C_L (pF)	Min	Typ.	Max	Min	Max		
Propagation delay time	t_{pLH} t_{pHL}	—	3.3 ± 0.3	15	—	5.8	8.4	1.0	10.0	ns
				50	—	8.3	11.9	1.0	13.5	
			5.0 ± 0.5	15	—	4.0	5.5	1.0	6.5	
				50	—	5.5	7.5	1.0	8.5	
3-state output enable time	t_{pZL} t_{pZH}	R_L = 1 kΩ	3.3 ± 0.3	15	—	8.5	13.2	1.0	15.5	ns
				50	—	11.0	16.7	1.0	19.0	
			5.0 ± 0.5	15	—	5.8	8.5	1.0	10.0	
				50	—	7.3	10.6	1.0	12.0	
3-state output disable time	t_{pLZ} t_{pHZ}	R_L = 1 kΩ	3.3 ± 0.3	50	—	11.5	15.8	1.0	18.0	ns
			5.0 ± 0.5	50	—	7.0	9.7	1.0	11.0	
Output to output skew	t_{osLH} t_{osHL}	(Note 1)	3.3 ± 0.3	50	—	—	1.5	—	1.5	ns
			5.0 ± 0.5	50	—	—	1.0	—	1.0	
Input capacitance	C_{IN}	DIR, $\overline{G}$		—	4	10	—	10		pF
Bus input capacitance	$C_{I/O}$	A_n, Bn		—	8	—	—	—		pF
Power dissipation capacitance	C_{PD}	(Note 2)		—	21	—	—	—		pF

Note 1: Parameter guaranteed by design.

$$t_{osLH} = |t_{pLHm} − t_{pLHn}|, \ t_{osHL} = |t_{pHLm} − t_{pHLn}|$$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC \ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \ (per \ bit)$$

Noise Characteristics (input: $t_r = t_f$ = 3 ns) (Note)

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
			V_{CC} (V)	Typ.	Max	
Quiet output maximum dynamic V_{OL}	V_{OLP}	C_L = 50 pF	5.0	0.7 (0.9)	1.0 (1.2)	V
Quiet output minimum dynamic V_{OL}	V_{OLV}	C_L = 50 pF	5.0	−0.7 (−0.9)	−1.0 (−1.2)	V
Minimum high level dynamic input voltage	V_{IHD}	C_L = 50 pF	5.0	—	3.5	V
Maximum low level dynamic input voltage	V_{ILD}	C_L = 50 pF	5.0	—	1.5	V

Note: The value in ( ) only applies to JEDEC SOP (FW) devices.

Input Equivalent Circuit
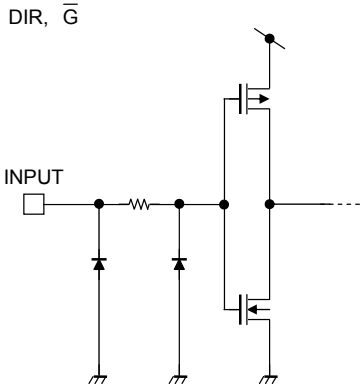
Bus Terminal Equivalent Circuit

DIR, $\overline{G}$

INPUT

A_n, B_n
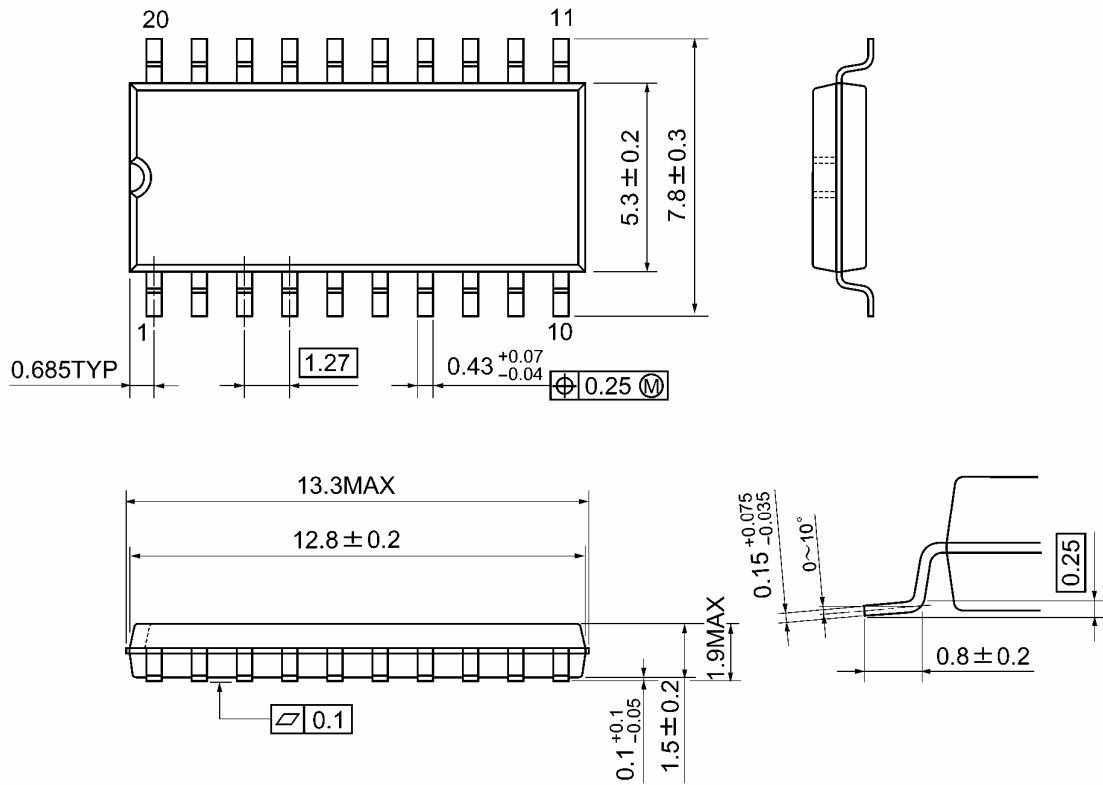
I/O
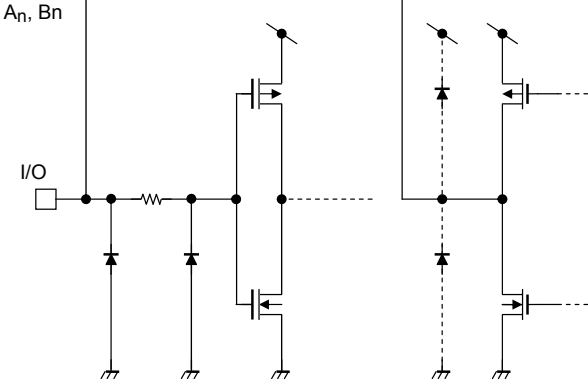
Package Dimensions

SOP20-P-300-1.27A   Unit: mm
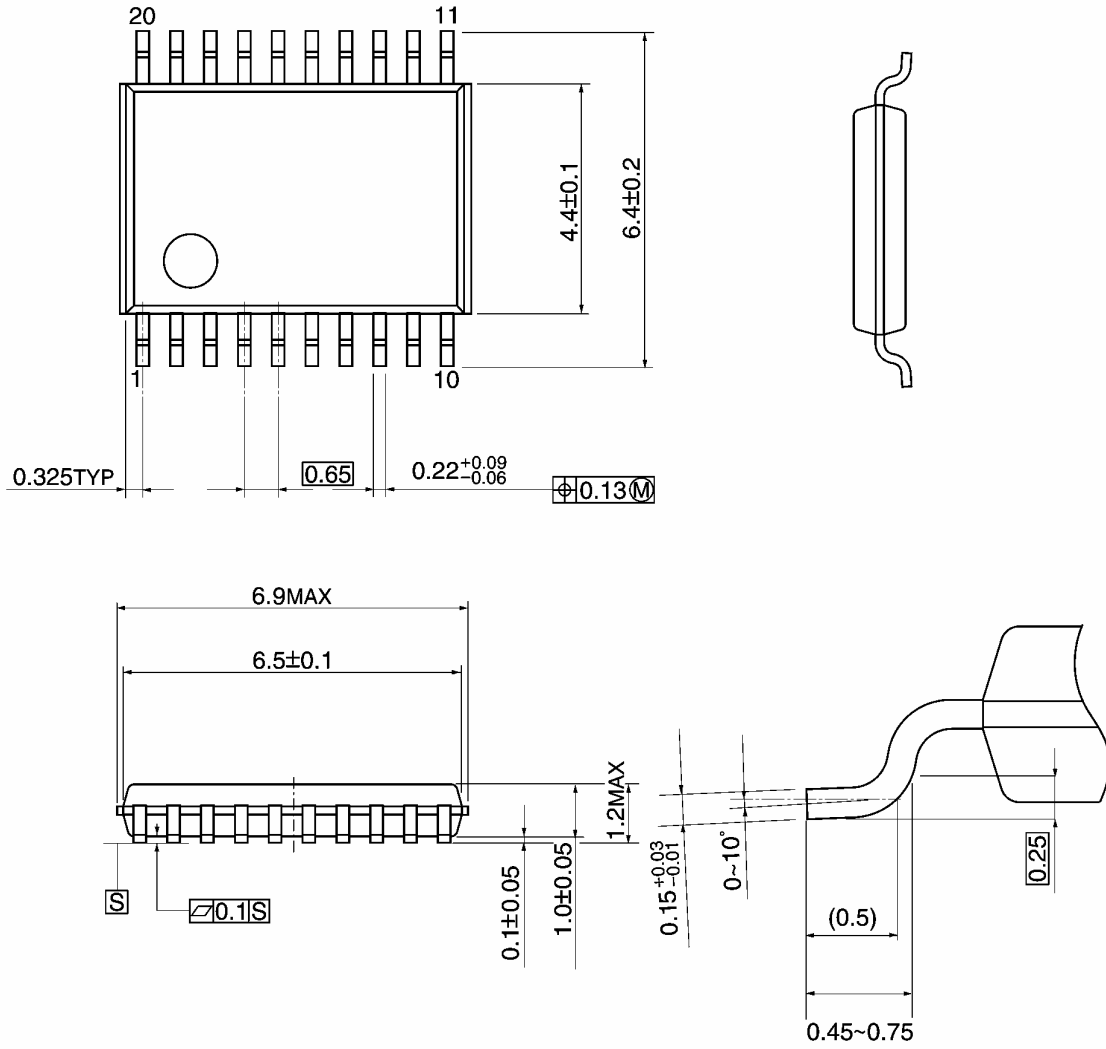

Weight: 0.22 g (typ.)
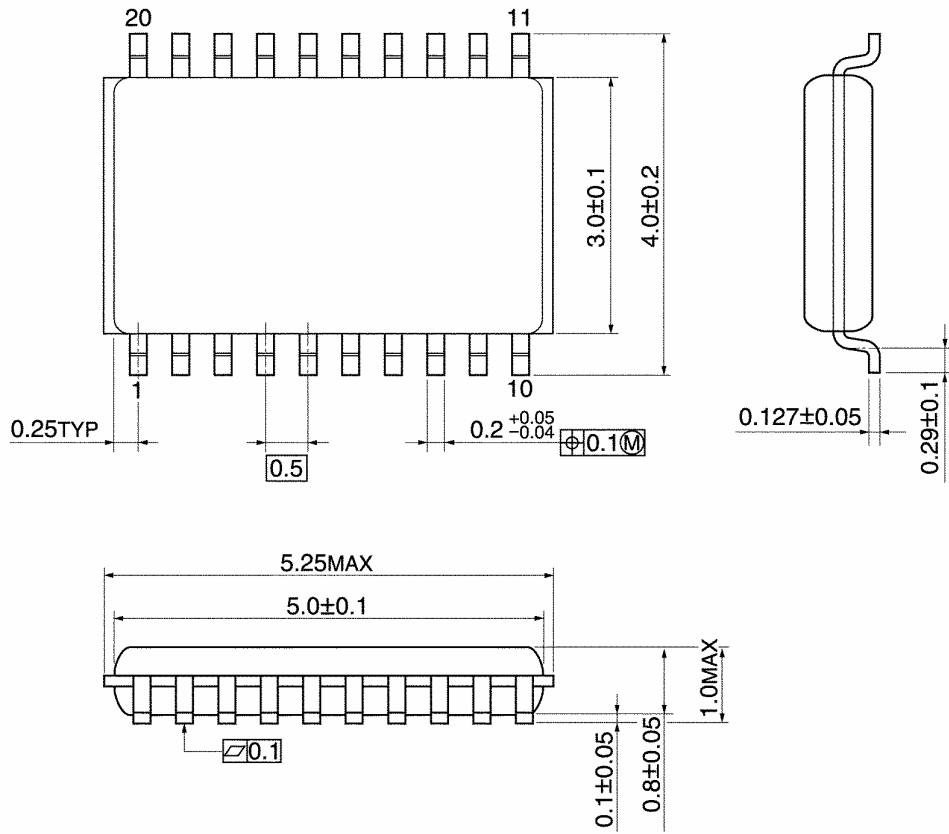
Package Dimensions

TSSOP20-P-0044-0.65A

Unit: mm

Weight: 0.08 g (typ.)

Package Dimensions

VSSOP20-P-0030-0.50   Unit: mm

Weight: 0.03 g (typ.)

RESTRICTIONS ON PRODUCT USE